

**RADIATION HARDENED
 POWER MOSFET
 THRU-HOLE (TO-205AF)**

**IRHF7330SE
 JANSR2N7463T2
 400V, N-CHANNEL
 REF: MIL-PRF-19500/675
 RAD Hard™ HEXFET® TECHNOLOGY**

Product Summary

Part Number	Radiation Level	RDS(on)	Id	QPL Part Number
IRHF7330SE	100K Rads (Si)	1.2Ω	3.0A	JANSR2N7463T2



International Rectifier's RADHard™ HEXFET® MOSFET technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low RDS(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Ultra Low RDS(on)
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
ID @ VGS = 12V, TC = 25°C	Continuous Drain Current	3.0	A
ID @ VGS = 12V, TC = 100°C	Continuous Drain Current	1.9	
IDM	Pulsed Drain Current ①	12	
PD @ TC = 25°C	Max. Power Dissipation	25	W
	Linear Derating Factor	0.2	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	140	mJ
IAR	Avalanche Current ①	3.0	A
EAR	Repetitive Avalanche Energy ①	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	6.7	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10 sec.)	
	Weight	0.98 (Typical)	g

For footnotes refer to the last page

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

Parameter		Min	Typ	Max	Units	Test Conditions
BVDSS	Drain-to-Source Breakdown Voltage	400	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBVDSS/ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.50	—	V/°C	Reference to 25°C, I _D = 1.0mA
RDS(on)	Static Drain-to-Source On-State Resistance	—	—	1.2	Ω	V _{GS} = 12V, I _D = 1.9A ④
VGS(th)	Gate Threshold Voltage	2.5	—	4.5	V	V _{DS} = V _{GS} , I _D = 1.0mA
gfs	Forward Transconductance	1.3	—	—	S (τ)	V _{DS} > 15V, I _{DS} = 1.9A ④
IDSS	Zero Gate Voltage Drain Current	—	—	50	μA	V _{DS} = 320V, V _{GS} = 0V
		—	—	250		V _{DS} = 320V, V _{GS} = 0V, T _J = 125°C
IGSS	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
IGSS	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Qg	Total Gate Charge	—	—	41	nC	V _{GS} = 12V, I _D = 3.0A V _{DS} = 200V
Qgs	Gate-to-Source Charge	—	—	7.0		
Qgd	Gate-to-Drain ('Miller') Charge	—	—	20		
td(on)	Turn-On Delay Time	—	—	35	ns	V _{DD} = 200V, I _D = 3.0A, V _{GS} = 12V, R _G = 7.5Ω
tr	Rise Time	—	—	62		
td(off)	Turn-Off Delay Time	—	—	58		
tf	Fall Time	—	—	58		
LS + LD	Total Inductance	—	7.0	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
Ciss	Input Capacitance	—	555	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
Coss	Output Capacitance	—	160	—		
Crss	Reverse Transfer Capacitance	—	60	—		

Source-Drain Diode Ratings and Characteristics

Parameter		Min	Typ	Max	Units	Test Conditions
IS	Continuous Source Current (Body Diode)	—	—	3.0	A	
ISM	Pulse Source Current (Body Diode) ①	—	—	12		
VSD	Diode Forward Voltage	—	—	1.4	V	T _J = 25°C, I _S = 3.0A, V _{GS} = 0V ④
trr	Reverse Recovery Time	—	—	516	nS	T _J = 25°C, I _F = 3.0A, di/dt ≤ 100A/μs
QRR	Reverse Recovery Charge	—	—	3.0	μC	V _{DD} ≤ 50V ④
ton	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by LS + LD.				

Thermal Resistance

Parameter		Min	Typ	Max	Units	Test Conditions
RthJC	Junction-to-Case	—	—	5.0	°C/W	Typical socket mount
RthJA	Junction-to-Ambient	—	—	175		

Note: Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100K Rads (Si)		Units	Test Conditions ⑧
		Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	400	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.5		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100		V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	50	μA	V _{DS} = 320V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source On-State Resistance ④	—	1.2	Ω	V _{GS} = 12V, I _D = 1.9A
V _{SD}	Diode Forward Voltage ④	—	1.4	V	V _{GS} = 0V, I _D = 3.0A

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm ²)	Energy (MeV)	Range (μm)	V _{DS} (V)				
				@V _{GS} =0V	@V _{GS} =-5V	@V _{GS} =-10V	@V _{GS} =-15V	@V _{GS} =-20V
Cu	28	285	43	325	325	325	325	—
Br	36.8	305	39	325	325	325	275	—

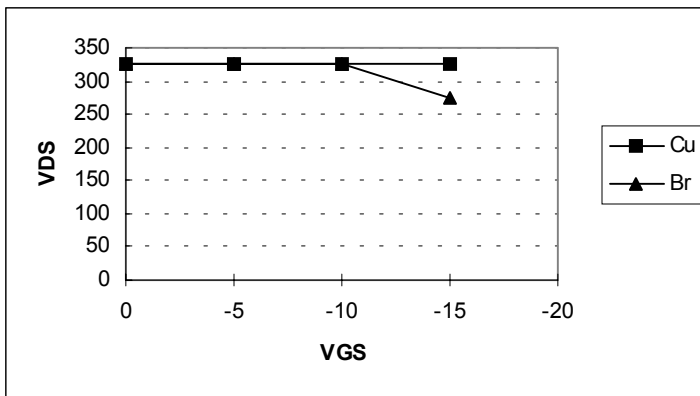


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

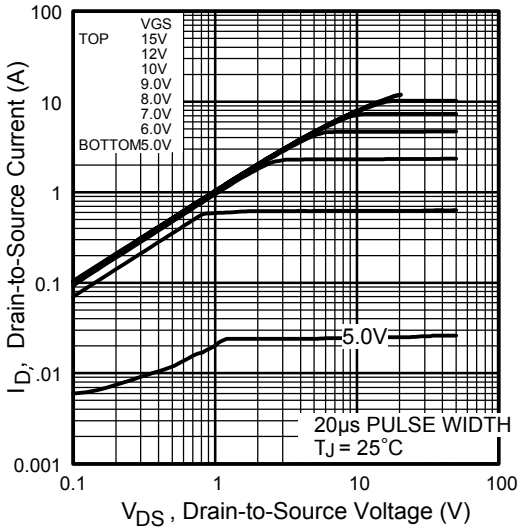


Fig 1. Typical Output Characteristics

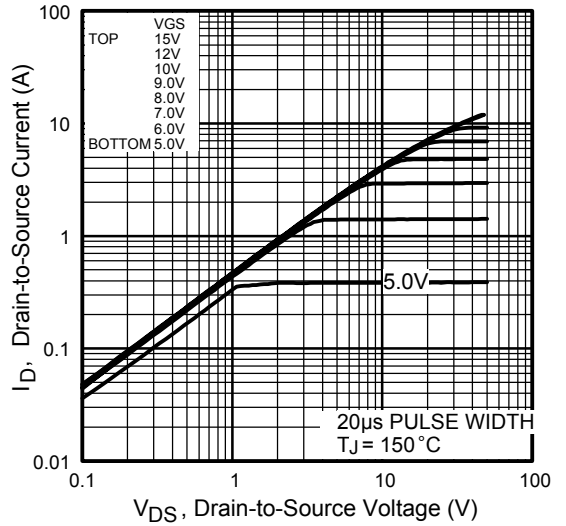


Fig 2. Typical Output Characteristics

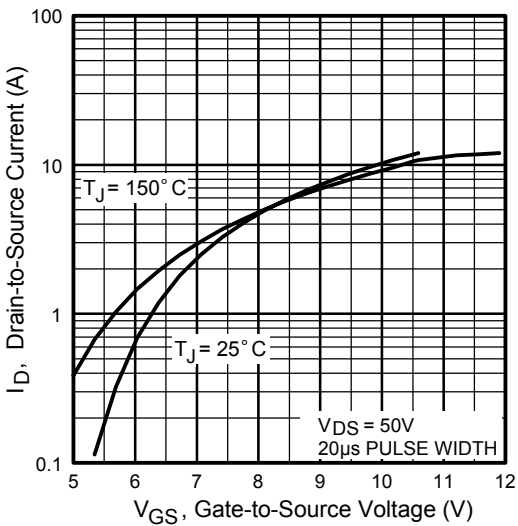


Fig 3. Typical Transfer Characteristics

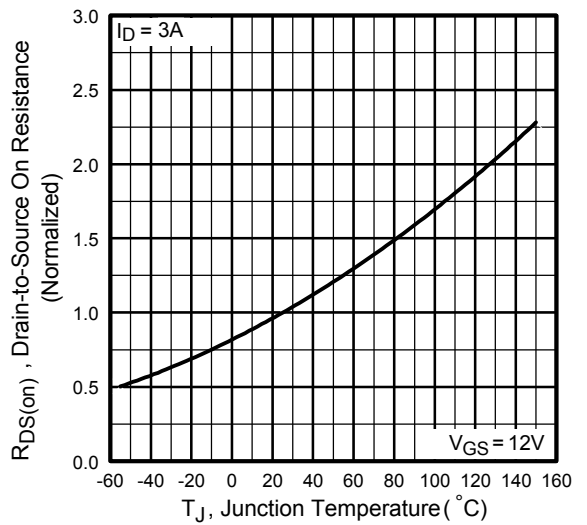


Fig 4. Normalized On-Resistance Vs. Temperature

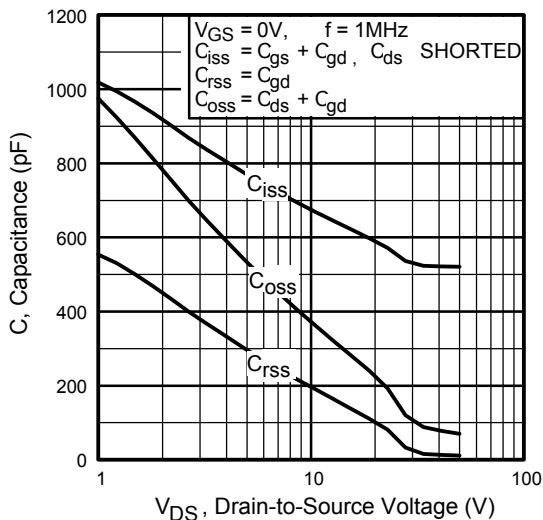


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

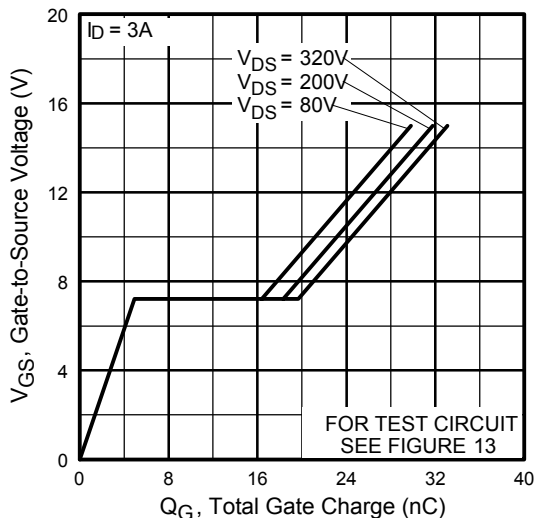


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

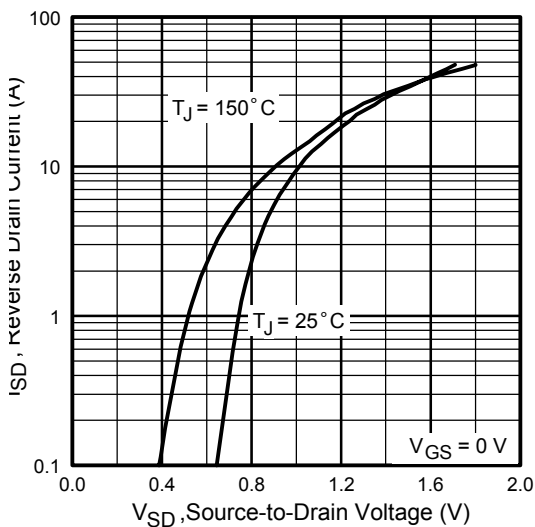


Fig 7. Typical Source-Drain Diode Forward Voltage

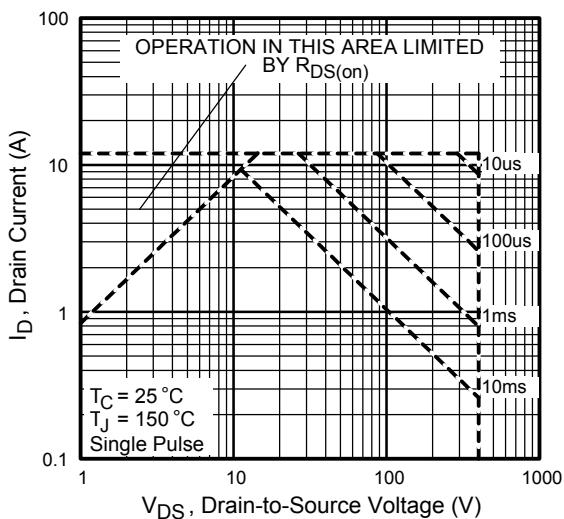


Fig 8. Maximum Safe Operating Area

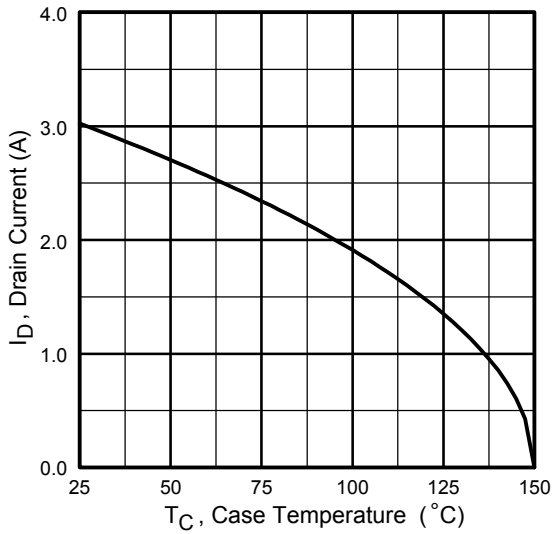


Fig 9. Maximum Drain Current Vs. Case Temperature

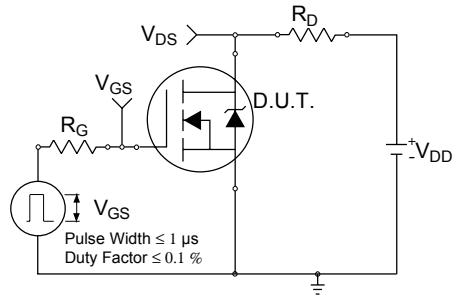


Fig 10a. Switching Time Test Circuit

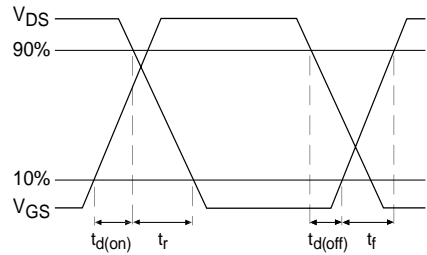


Fig 10b. Switching Time Waveforms

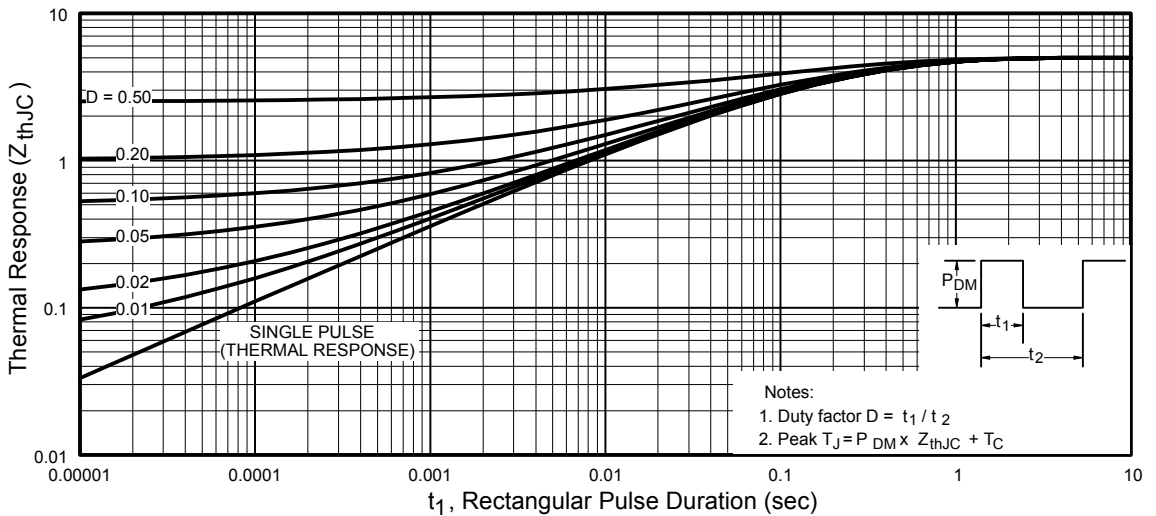


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

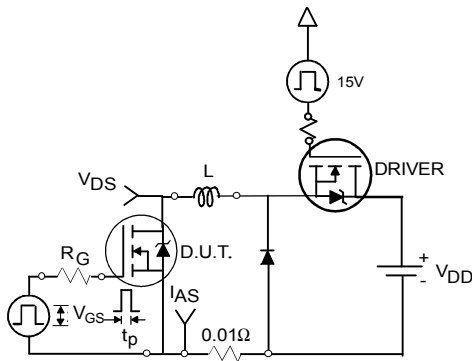


Fig 12a. Unclamped Inductive Test Circuit

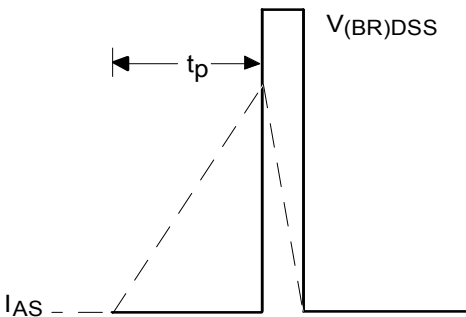


Fig 12b. Unclamped Inductive Waveforms

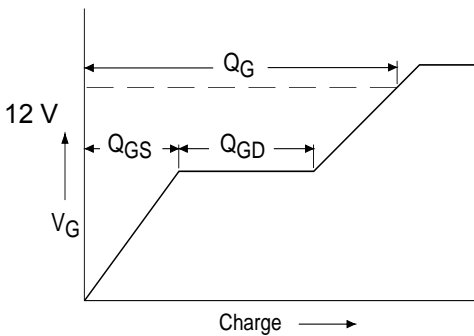


Fig 13a. Basic Gate Charge Waveform

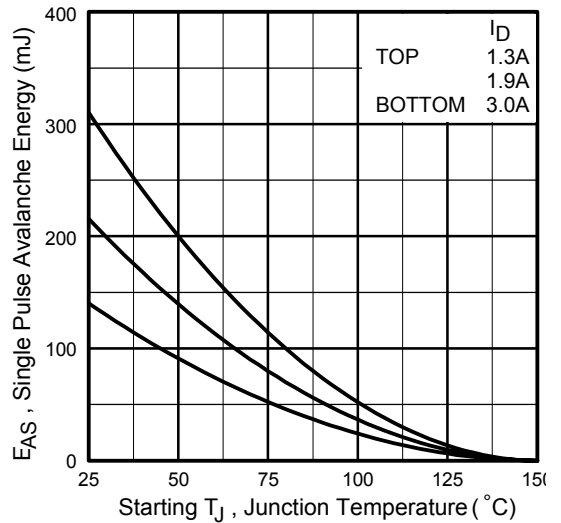


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

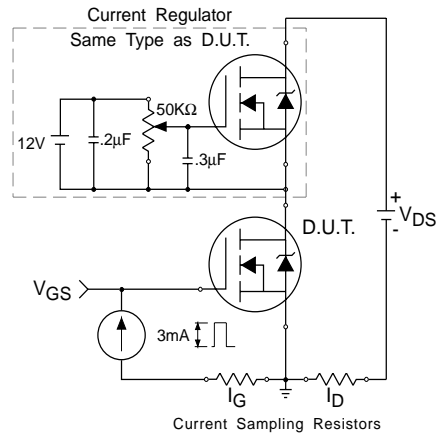
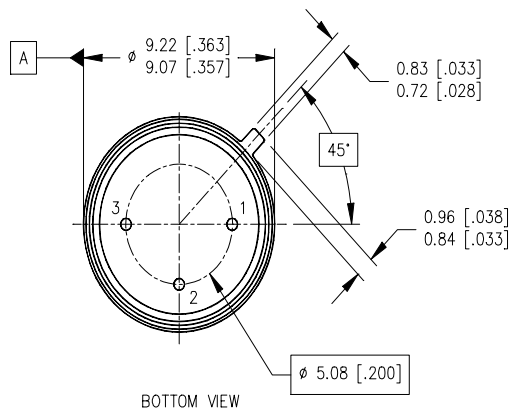
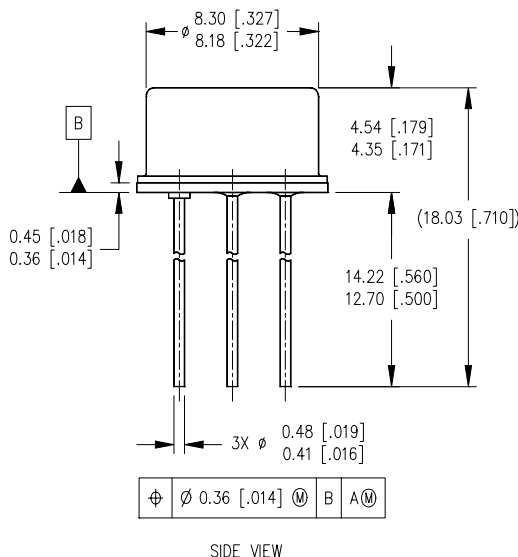


Fig 13b. Gate Charge Test Circuit

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 50V$, starting $T_J = 25^\circ C$, $L = 31\text{ mH}$
Peak $I_L = 3.0A$, $V_{GS} = 12V$
- ③ $I_{SD} \leq 3.0A$, $di/dt \leq 400A/\mu s$,
 $V_{DD} \leq 400V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300\ \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
320 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions —TO-205AF (Modified TO-39)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME 14.5M-1994.
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. CONFORMS TO JEDEC OUTLINE TO-205AF (TO-39).

LEGEND

- 1- SOURCE
- 2- GATE
- 3- DRAIN

International
IR Rectifier

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